

Bruno Daudin

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#	Paper	IF	Citations
351	Stranski-Krastanov growth mode during the molecular beam epitaxy of highly strained GaN. <i>Physical Review B</i> , 1997 , 56, R7069-R7072	3.3	323
350	Blue-light emission from GaN self-assembled quantum dots due to giant piezoelectric effect. <i>Physical Review B</i> , 1998 , 58, R15989-R15992	3.3	239
349	Growth kinetics and optical properties of self-organized GaN quantum dots. <i>Journal of Applied Physics</i> , 1998 , 83, 7618-7624	2.5	200
348	From nucleation to growth of catalyst-free GaN nanowires on thin AlN buffer layer. <i>Applied Physics Letters</i> , 2007 , 91, 251902	3.4	185
347	Polarity determination of GaN films by ion channeling and convergent beam electron diffraction. <i>Applied Physics Letters</i> , 1996 , 69, 2480-2482	3.4	166
346	Direct comparison of recombination dynamics in cubic and hexagonal GaN/AlN quantum dots. <i>Physical Review B</i> , 2003 , 68,	3.3	141
345	Dynamically stable gallium surface coverages during plasma-assisted molecular-beam epitaxy of (0001) GaN. <i>Journal of Applied Physics</i> , 2002 , 91, 9638	2.5	141
344	Improved quality GaN grown by molecular beam epitaxy using In as a surfactant. <i>Applied Physics Letters</i> , 1998 , 73, 2642-2644	3.4	140
343	Self-assembled InGaN quantum dots grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2000 , 76, 1570-1572	3.4	136
342	Surfactant effect of gallium during molecular-beam epitaxy of GaN on AlN (0001). <i>Physical Review B</i> , 2001 , 64,	3.3	122
341	Gallium adsorption on (0001) GaN surfaces. <i>Physical Review B</i> , 2003 , 67,	3.3	118
340	Strain relaxation in (0001) AlN/GaN heterostructures. <i>Physical Review B</i> , 2001 , 63,	3.3	99
339	Thermodynamic properties of the gadolinium gallium garnet, Gd ₃ Ga ₅ O ₁₂ , between 0.05 and 25 K. <i>Journal of Magnetism and Magnetic Materials</i> , 1982 , 27, 315-322	2.8	97
338	Structure of GaN quantum dots grown under modified Stranski-Krastanov conditions on AlN. <i>Journal of Applied Physics</i> , 2003 , 94, 2254-2261	2.5	93
337	Structural and optical properties of InGaN/GaN nanowire heterostructures grown by PA-MBE. <i>Nanotechnology</i> , 2011 , 22, 075601	3.4	92
336	Quantitative characterization of GaN quantum-dot structures in AlN by high-resolution transmission electron microscopy. <i>Applied Physics Letters</i> , 1999 , 74, 3287-3289	3.4	92
335	Polarity of GaN nanowires grown by plasma-assisted molecular beam epitaxy on Si(111). <i>Physical Review B</i> , 2011 , 84,	3.3	89

334	Phonon deformation potentials of wurtzite AlN. <i>Journal of Applied Physics</i> , 2003 , 93, 2065-2068	2.5	88
333	Evidence for quantum-confined Stark effect in GaN/AlN quantum dots in nanowires. <i>Physical Review B</i> , 2009 , 80,	3.3	87
332	Exciton and biexciton luminescence from single GaN/AlN quantum dots in nanowires. <i>Nano Letters</i> , 2008 , 8, 2092-6	11.5	86
331	Intersubband spectroscopy of doped and undoped GaN/AlN quantum wells grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2003 , 83, 5196-5198	3.4	79
330	Nucleation mechanism of GaN nanowires grown on (111) Si by molecular beam epitaxy. <i>Nanotechnology</i> , 2009 , 20, 415602	3.4	78
329	Self-assembled zinc blende GaN quantum dots grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2000 , 77, 809-811	3.4	78
328	Surfactant effect of In for AlGaIn growth by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2003 , 93, 1550-1556	2.5	72
327	Preferential nucleation of GaN quantum dots at the edge of AlN threading dislocations. <i>Applied Physics Letters</i> , 1999 , 75, 2632-2634	3.4	72
326	Growth and optical properties of GaN/AlN quantum wells. <i>Applied Physics Letters</i> , 2003 , 82, 4154-4156	3.4	71
325	High-temperature ion beam synthesis of cubic SiC. <i>Journal of Applied Physics</i> , 1990 , 67, 2908-2912	2.5	71
324	The structural properties of GaN/AlN core-shell nanocolumn heterostructures. <i>Nanotechnology</i> , 2010 , 21, 415702	3.4	67
323	Strain distribution in GaN/AlN quantum-dot superlattices. <i>Applied Physics Letters</i> , 2005 , 87, 203112	3.4	67
322	Effects of electron irradiation and annealing on ferroelectric vinylidene fluoride-trifluoroethylene copolymers. <i>Journal of Applied Physics</i> , 1987 , 62, 994-997	2.5	67
321	Plastic strain relaxation of nitride heterostructures. <i>Journal of Applied Physics</i> , 2004 , 95, 1127-1133	2.5	66
320	Phonons in a strained hexagonal GaN/AlN superlattice. <i>Applied Physics Letters</i> , 1999 , 74, 703-705	3.4	66
319	Transmission electron microscopy structural characterisation of GaN layers grown on (0001) sapphire. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997 , 50, 61-71	3.1	64
318	Growth mechanism and properties of InGaIn insertions in GaN nanowires. <i>Nanotechnology</i> , 2012 , 23, 135703	3.4	63
317	Low temperature sapphire nitridation: A clue to optimize GaN layers grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1999 , 85, 1550-1555	2.5	63

316	Si Donor Incorporation in GaN Nanowires. <i>Nano Letters</i> , 2015 , 15, 6794-801	11.5	61
315	Optical properties of GaN quantum dots grown on nonpolar (11-20) SiC by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2005 , 86, 171901	3.4	59
314	How to grow cubic GaN with low hexagonal phase content on (001) SiC by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1998 , 84, 2295-2300	2.5	59
313	Submicrometre resolved optical characterization of green nanowire-based light emitting diodes. <i>Nanotechnology</i> , 2011 , 22, 345705	3.4	58
312	Growth kinetics of N-face polarity GaN by plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2004 , 84, 3684-3686	3.4	58
311	Growth, structural and optical properties of AlGaIn nanowires in the whole composition range. <i>Nanotechnology</i> , 2013 , 24, 115704	3.4	56
310	Probing exciton localization in nonpolar GaN/AlN quantum dots by single-dot optical spectroscopy. <i>Physical Review B</i> , 2007 , 75,	3.3	56
309	Identification of III-N nanowire growth kinetics via a marker technique. <i>Nanotechnology</i> , 2010 , 21, 295605	3.4	53
308	Plasma-assisted molecular beam epitaxy growth of GaN nanowires using indium-enhanced diffusion. <i>Applied Physics Letters</i> , 2008 , 93, 183109	3.4	53
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306	Influence of AlN overgrowth on structural properties of GaN quantum wells and quantum dots grown by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2004 , 96, 1104-1110	2.5	51
305	GaN islanding by spontaneous rearrangement of a strained two-dimensional layer on (0001) AlN. <i>Applied Physics Letters</i> , 2002 , 81, 3064-3066	3.4	51
304	The influence of AlN buffer over the polarity and the nucleation of self-organized GaN nanowires. <i>Journal of Applied Physics</i> , 2015 , 117, 245303	2.5	49
303	Layer-by-layer growth of AlN and GaN by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 1997 , 182, 1-5	1.6	49
302	GaN quantum dots doped with Eu. <i>Applied Physics Letters</i> , 2004 , 84, 206-208	3.4	48
301	Molecular-beam epitaxial growth and characterization of quaternary IIIbNitride compounds. <i>Journal of Applied Physics</i> , 2003 , 94, 3121-3127	2.5	48
300	Nucleation of GaN nanowires grown by plasma-assisted molecular beam epitaxy: The effect of temperature. <i>Journal of Crystal Growth</i> , 2011 , 334, 177-180	1.6	45
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- 297 Vertical transport in group III-nitride heterostructures and application in AlN/GaN resonant tunneling diodes. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2004**, 1, 2210-2227 45
- 296 In situ study of self-assembled GaN nanowires nucleation on Si(111) by plasma-assisted molecular beam epitaxy. *Applied Physics Letters*, **2012**, 100, 212107 3-4 44
- 295 Angular dispersion of polar phonons in a hexagonal GaN/AlN superlattice. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2001**, 82, 27-29 3-1 44
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- 281 Surface optical phonon modes in GaN nanowire arrays: Dependence on nanowire density and diameter. *Physical Review B*, **2012**, 85, 3-3 33

280	Optical transitions in Eu ³⁺ ions in GaN:Eu grown by molecular beam epitaxy. <i>Physical Review B</i> , 2006 , 73,	3.3	33
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278	Optical anisotropy and light extraction efficiency of MBE grown GaN nanowires epilayers. <i>Optics Express</i> , 2011 , 19, 527-39	3.3	32
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272	Inelastic Light Scattering by Phonons in Hexagonal GaN/AlN Nanostructures. <i>Physica Status Solidi A</i> , 2001 , 183, 157-161		28
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270	Surface stoichiometry determination using reflection high-energy electron diffraction and atomic-layer epitaxy: The case of ZnTe(100). <i>Physical Review B</i> , 1995 , 52, 7822-7825	3.3	28
269	Quantum Dot-Like Behavior of Compositional Fluctuations in AlGaIn Nanowires. <i>Nano Letters</i> , 2016 , 16, 960-6	11.5	27
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267	Lifetime Measurements Well below the Optical Diffraction Limit. <i>ACS Photonics</i> , 2016 , 3, 1157-1163	6.3	26
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264	Fine optical spectroscopy of the 3.45 eV emission line in GaN nanowires. <i>Journal of Applied Physics</i> , 2013 , 113, 043102	2.5	25
263	Epitaxial Growth of GaN, AlN and InN: 2D/3D Transition and Surfactant Effects. <i>Physica Status Solidi A</i> , 1999 , 176, 621-627		25

262	Polar and nonpolar GaN quantum dots. <i>Journal of Physics Condensed Matter</i> , 2008 , 20, 473201	1.8	24
261	Grazing-incidence diffraction anomalous fine structure: Application to the structural investigation of group-III nitride quantum dots. <i>Physical Review B</i> , 2007 , 75,	3.3	24
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257	Optical and morphological properties of GaN quantum dots doped with Tm. <i>Physical Review B</i> , 2005 , 71,	3.3	23
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255	Chemical defects induced in P(VDF-TrFe) by electron irradiation. <i>Radiation Effects and Defects in Solids</i> , 1991 , 118, 117-124	0.9	23
254	Enhanced red emission from praseodymium-doped GaN nanowires by defect engineering. <i>Acta Materialia</i> , 2013 , 61, 3278-3284	8.4	22
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238	Self-Assembled GaN Quantum Dots Grown by Plasma-Assisted Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, 1892-1895	1.4	20
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